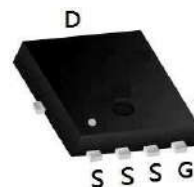


30V N-Channel MOSFET

Description:

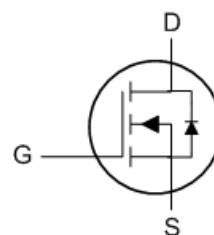
- Advanced Trench MOS Technology
- Low Gate Charge
- Low $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available



PRPAK3X3 Pin Configuration

Applications:

- Power Management in Desktop Computer or DC/DC Converters.
- Isolated DC/DC Converters in Telecom and Industrial.



Product Summary

BVDSS	RDS(ON)	ID
30V	5.2mΩ	32A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	32	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	26	A
I_{DM}	Pulsed Drain Current ²	100	A
EAS	Single Pulse Avalanche Energy ³	61.3	mJ
I_{AS}	Avalanche Current	35	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation ⁴	25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	60	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5	$^\circ\text{C/W}$

N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	---	4.5	5.2	$m\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	7.2	9	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.7	2.2	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=30V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	65	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	0.8	1.7	2.6	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=10V, I_D=20A$	---	9	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	3.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3\Omega, I_D=20A$	---	7	---	ns
T_r	Rise Time		---	18.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	19.5	---	
T_f	Fall Time		---	3.4	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	1113	---	pF
C_{oss}	Output Capacitance		---	436	---	
C_{rss}	Reverse Transfer Capacitance		---	55	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	20	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=35A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N- Channel Typical Characteristics

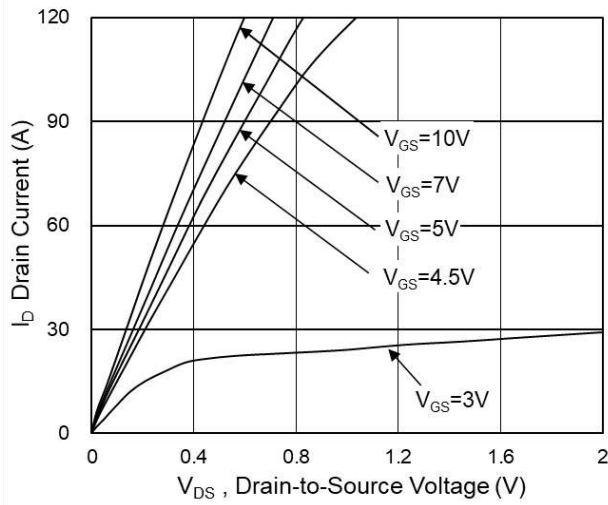


Fig.1 Typical Output Characteristics

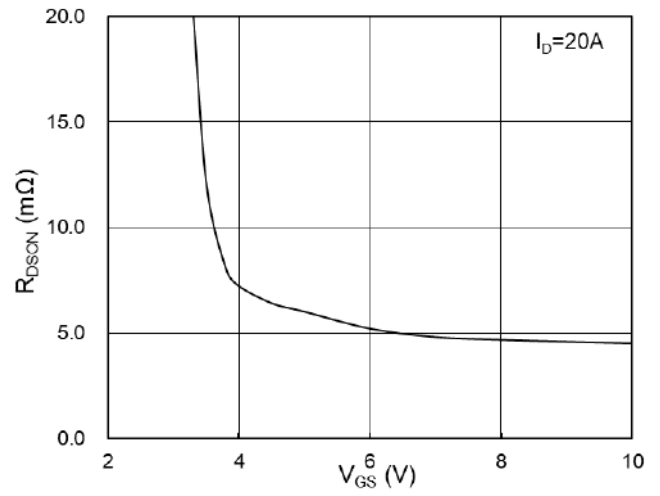


Fig.2 On-Resistance vs G-S Voltage

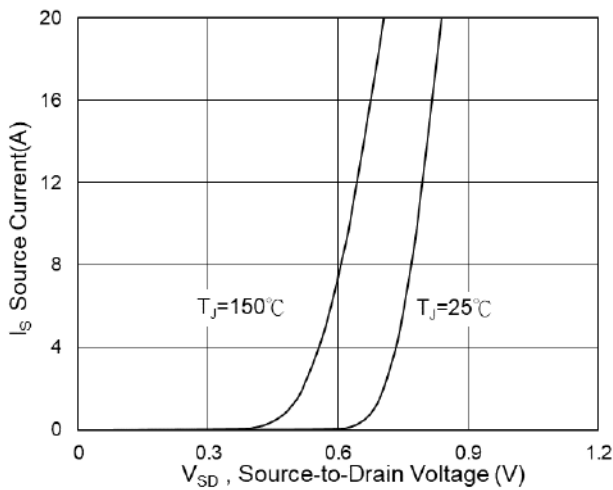


Fig.3 Source Drain Forward Characteristics

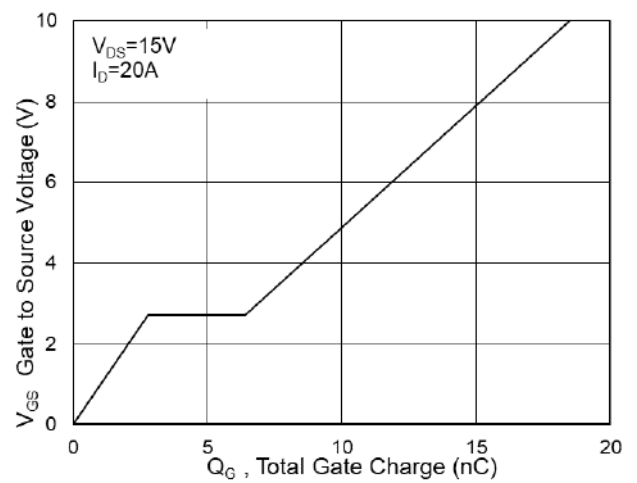


Fig.4 Gate-Charge Characteristics

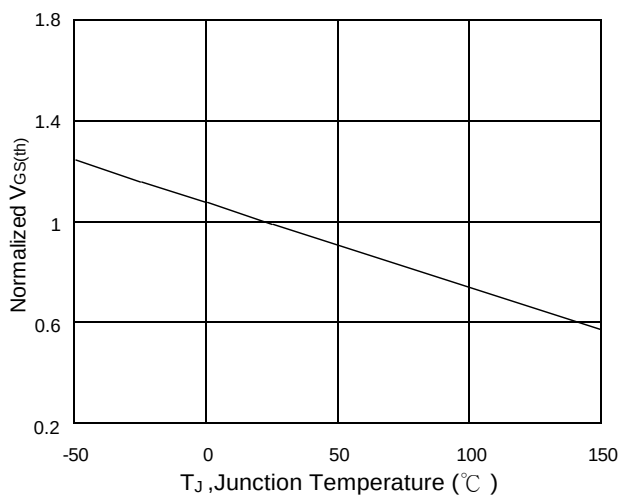


Fig.5 Normalized $V_{GS(th)}$ vs T_J

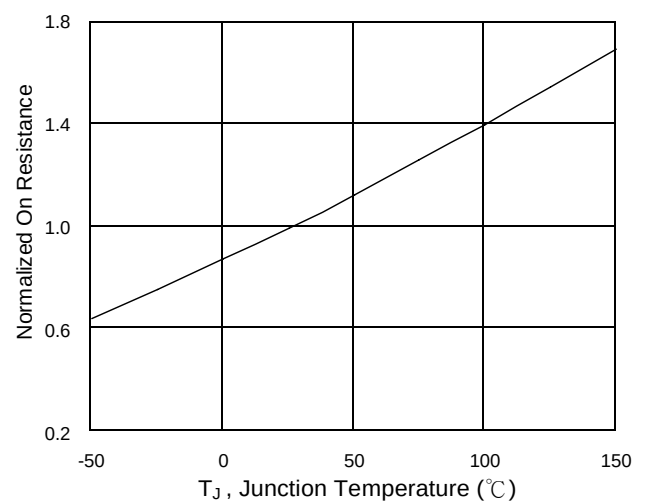


Fig.6 Normalized $R_{DS(on)}$ vs T_J

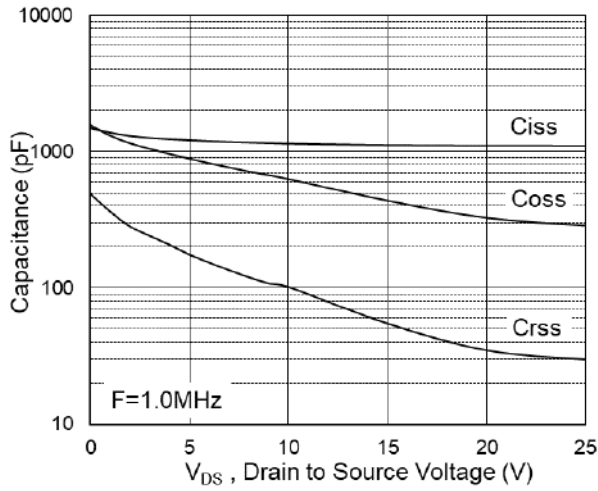


Fig.7 Capacitance

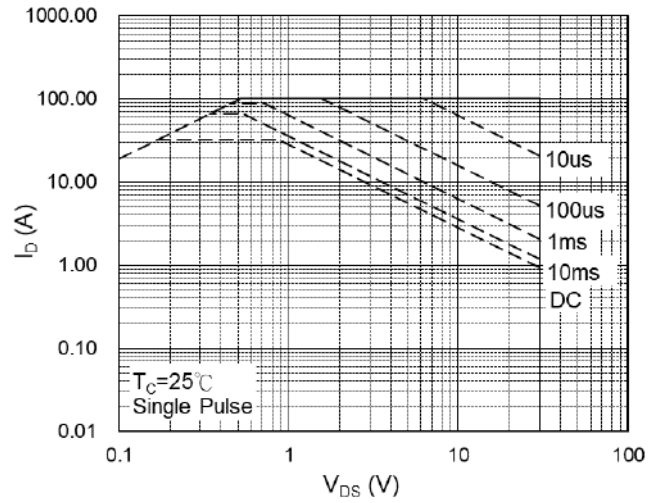


Fig.8 Safe Operating Area

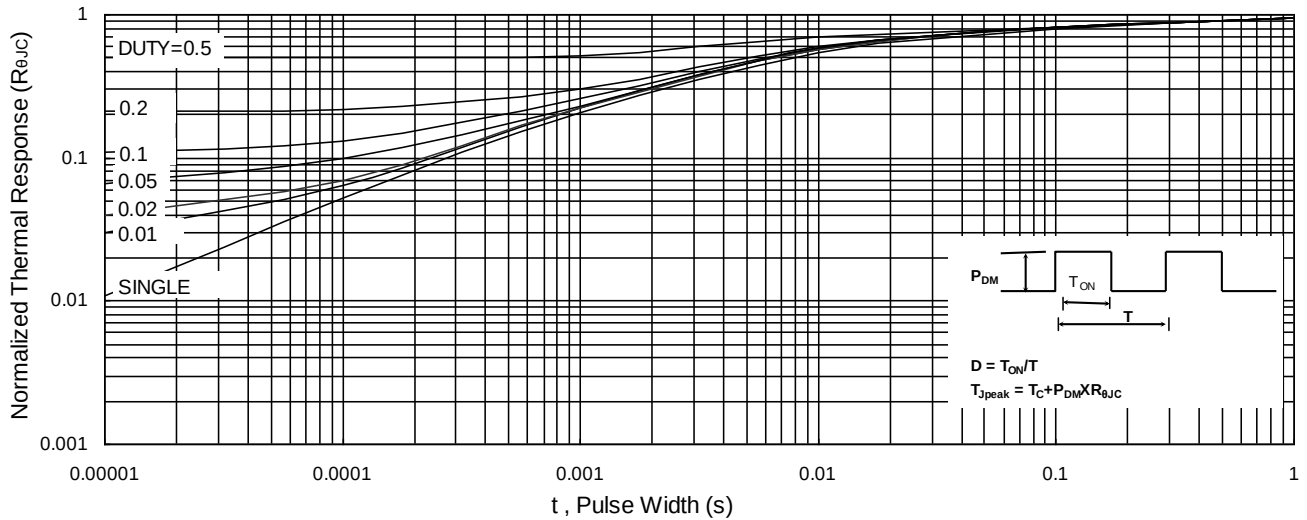


Fig.9 Normalized Maximum Transient Thermal Impedance

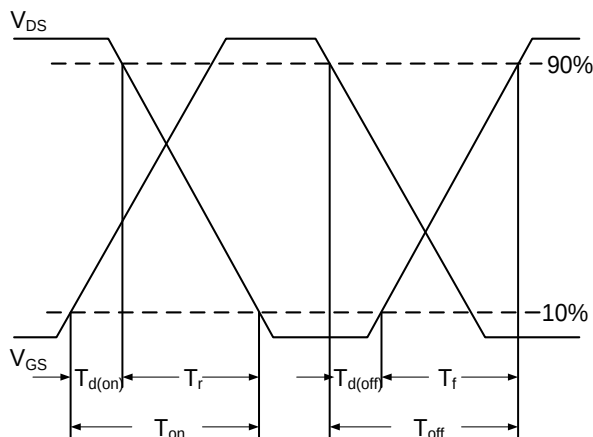


Fig.10 Switching Time Waveform

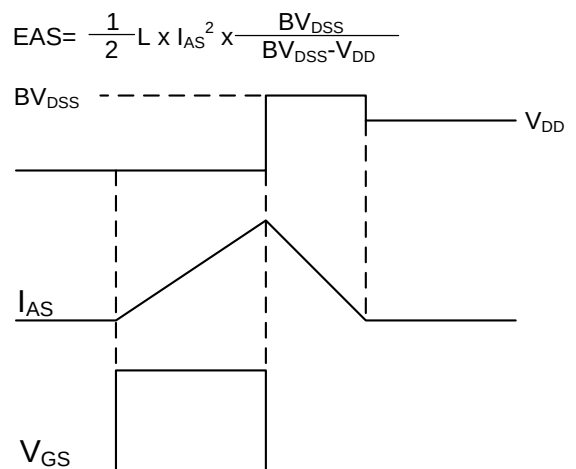


Fig.11 Unclamped Inductive Switching Waveform